

Iddo Amit

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

22
papers

536
citations

13
h-index

23
g-index

23
ext. papers

609
ext. citations

10
avg, IF

3.59
L-index

#	Paper	IF	Citations
22	Boron Monolayer Doping: Role of Oxide Capping Layer, Molecular Fragmentation, and Doping Uniformity at the Nanoscale. <i>Advanced Materials Interfaces</i> , 2020 , 7, 1902198	4.6	6
21	Laser-writable high-k dielectric for van der Waals nanoelectronics. <i>Science Advances</i> , 2019 , 5, eaau0906	14.3	35
20	Energy dispersive spectroscopic measurement of charge traps in MoTe ₂ . <i>Physical Review B</i> , 2019 , 100,	3.3	1
19	Accurate Method To Determine the Mobility of Transition-Metal Dichalcogenides with Incomplete Gate Screening. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 44406-44412	9.5	3
18	Ultrahigh Performance Nanoengineered Graphene-Concrete Composites for Multifunctional Applications. <i>Advanced Functional Materials</i> , 2018 , 28, 1705183	15.6	101
17	Sub 20 meV Schottky barriers in metal/MoTe ₂ junctions. <i>2D Materials</i> , 2018 , 5, 025023	5.9	15
16	Strain-engineered inverse charge-funnelling in layered semiconductors. <i>Nature Communications</i> , 2018 , 9, 1652	17.4	25
15	Functionalised hexagonal-domain graphene for position-sensitive photodetectors. <i>Nanotechnology</i> , 2017 , 28, 124004	3.4	9
14	Role of Charge Traps in the Performance of Atomically Thin Transistors. <i>Advanced Materials</i> , 2017 , 29, 1605598	24	37
13	High-Mobility and High-Optical Quality Atomically Thin WS ₂ . <i>Scientific Reports</i> , 2017 , 7, 14911	4.9	54
12	Impact of Dopant Compensation on Graded p-n Junctions in Si Nanowires. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 128-34	9.5	8
11	Multiple State Electrostatically Formed Nanowire Transistors. <i>IEEE Electron Device Letters</i> , 2015 , 36, 6514-6517	11.5	13
10	Tunable diameter electrostatically formed nanowire for high sensitivity gas sensing. <i>Nano Research</i> , 2015 , 8, 2206-2215	10	30
9	Potential barrier height at the grain boundaries of a poly-silicon nanowire. <i>Nanotechnology</i> , 2015 , 26, 355201	3.4	4
8	Density and energy distribution of interface states in the grain boundaries of polysilicon nanowire. <i>Nano Letters</i> , 2014 , 14, 6190-4	11.5	12
7	Parallel p-n junctions across nanowires by one-step ex situ doping. <i>ACS Nano</i> , 2014 , 8, 8357-62	16.7	27
6	Barrier height measurement of metal contacts to Si nanowires using internal photoemission of hot carriers. <i>Nano Letters</i> , 2013 , 13, 6183-8	11.5	26

5	Spatially resolved correlation of active and total doping concentrations in VLS grown nanowires. <i>Nano Letters</i> , 2013 , 13, 2598-604	11.5	39
4	Specific and label-free femtomolar biomarker detection with an electrostatically formed nanowire biosensor. <i>NPG Asia Materials</i> , 2013 , 5, e41-e41	10.3	44
3	Contact doping of silicon wafers and nanostructures with phosphine oxide monolayers. <i>ACS Nano</i> , 2012 , 6, 10311-8	16.7	44
2	Molecular gating of transistors by amine-terminated layers. <i>Applied Surface Science</i> , 2012 , 258, 4069-4072	7	1
1	The effect of nonideal polar monolayers on molecular gated transistors. <i>ACS Applied Materials & Interfaces</i> , 2010 , 2, 2289-92	9.5	2